

VOLTAGE RANGE: 20 - 100V

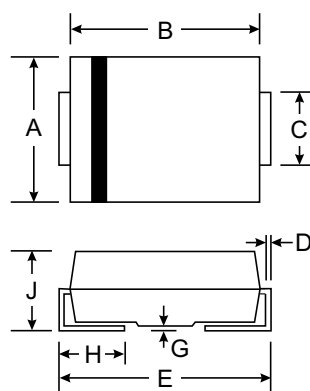
CURRENT: 1.0 A

Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: SMA/DO-214AC, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.064 grams (approx.)



SMA(DO-214AC)		
Dim	Min	Max
A	2.29	2.92
B	4.00	4.60
C	1.27	1.63
D	0.15	0.31
E	4.80	5.59
G	0.10	0.20
H	0.76	1.52
J	2.01	2.62
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SS12	SS13	SS14	SS15	SS16	SS18	SS110	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	V
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	70	V
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	V
Maximum average forward rectified current at T _L (see fig.1)	I _(AV)	1.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	40.0							A
Maximum instantaneous forward voltage at 1.0A	V _F	0.45	0.55		0.70		0.85		V
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	0.5							mA
		6.0			5.0				
Typical junction capacitance (NOTE 1)	C _J	110			90				pF
Typical thermal resistance (NOTE 2)		88.0							°C/W
Operating junction temperature range	T _J	-65 to +125			-65 to +150				°C
Storage temperature range	T _{STG}	-65 to +150							°C

Note:

1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas

RATINGS AND CHARACTERISTIC CURVES SS12 THRU SS110

